

b) Amendments to the Claims:

Kindly cancel claims 5-16 without prejudice or disclaimer and amend claims 1-3 as follows. The detailed listing of all the claims that are or were in the application is provided.

--1. (Currently Amended) A method of forming a silicon-based thin film comprising effecting high frequency plasma CVD using a source gas comprising a silicon halide and hydrogen, wherein the value of Q defined by $Q = P_O \times P_R / S/d$ is 50 or more, wherein $P_O(W)$ is a supplied power, $S (cm^2)$ is ~~the~~ an area of a high frequency introducing electrode, $d (cm)$ is a distance between the high frequency introducing electrode and a substrate, and $P_R (mTorr)$ is a pressure.

2. (Currently Amended) The method according to claim 1, wherein the silicon halide contains at least one ~~element~~ of fluorine ~~and~~ or chlorine.

3. (Currently Amended) The method according to claim 1, wherein ~~the~~ a flow rate of the hydrogen of the source gas is not less than the flow rate of the silicon halide.

4. (Original) The method according to claim 1, wherein the pressure P_R is 50 mTorr or more.

Claims 5-16 (Cancelled)